

# Richard ArÅ's

## List of Publications by Year in descending order

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Version: 2024-02-01

40  
papers

597  
citations

687363

13  
h-index

610901

24  
g-index

40  
all docs

40  
docs citations

40  
times ranked

516  
citing authors

#	ARTICLE	IF	CITATIONS
1	In-situ Transmission Electron Microscopy Observation of Germanium Growth on Freestanding Graphene: Unfolding Mechanism of 3D Crystal Growth During Van der Waals Epitaxy. <i>Small</i> , 2022, 18, e2101890.	10.0	5
2	Probing the coupling between the components in a graphene-mesoporous germanium nanocomposite using high-pressure Raman spectroscopy. <i>Nanoscale Advances</i> , 2021, 3, 2577-2584.	4.6	2
3	Shape control of cathodized germanium oxide nanoparticles. <i>Electrochemistry Communications</i> , 2021, 122, 106906.	4.7	6
4	Ultrafast photocarrier dynamics in Fe-implanted InGaAs polycrystalline photoconductive materials. <i>Journal of Physics Condensed Matter</i> , 2021, 33, 385701.	1.8	1
5	On the Test Particle Monte-Carlo method to solve the steady state Boltzmann equation, the congruity of its results with experiments and its potential for shared memory parallelism. <i>Journal of Computational Physics</i> , 2021, 444, 110590.	3.8	1
6	Structural, optical and terahertz properties of graphene-mesoporous silicon nanocomposites. <i>Nanoscale Advances</i> , 2020, 2, 340-346.	4.6	8
7	Optimized duplicated-junction solar cells: An innovative approach for energy harvesting at ultra-high concentrations. <i>AIP Conference Proceedings</i> , 2020, , .	0.4	2
8	Integration of 3D nanographene into mesoporous germanium. <i>Nanoscale</i> , 2020, 12, 23984-23994.	5.6	6
9	Terahertz photoconductivity and photocarrier dynamics in graphene-mesoporous silicon nanocomposites. <i>Physical Review B</i> , 2020, 102, .	3.2	1
10	Effect of sintering germanium epilayers on dislocation dynamics: From theory to experimental observation. <i>Acta Materialia</i> , 2020, 200, 608-618.	7.9	2
11	Cost-effective energy harvesting at ultra-high concentration with duplicated concentrated photovoltaic solar cells. <i>Energy Science and Engineering</i> , 2020, 8, 2760-2770.	4.0	8
12	AlN grown by CBE for power device applications. <i>AIP Advances</i> , 2020, 10, 065123.	1.3	0
13	Engineering dislocations and nanovoids for high-efficiency III-V photovoltaic cells on silicon. <i>AIP Conference Proceedings</i> , 2020, , .	0.4	2
14	Uprooting defects to enable high-performance III-V optoelectronic devices on silicon. <i>Nature Communications</i> , 2019, 10, 4322.	12.8	44
15	Graphene-porous semiconductor nanocomposites scalable synthesis for energy applications. <i>Journal of Physics: Conference Series</i> , 2019, 1407, 012069.	0.4	0
16	A porous Ge/Si interface layer for defect-free III-V multi-junction solar cells on silicon. , 2019, , .		5
17	Tunable conductivity in mesoporous germanium. <i>Nanotechnology</i> , 2018, 29, 215701.	2.6	17
18	Extreme temperature stability of thermally insulating graphene-mesoporous-silicon nanocomposite. <i>Nanotechnology</i> , 2018, 29, 145701.	2.6	9

#	ARTICLE	IF	CITATIONS
19	Challenges and strategies for implementing the vertical epitaxial heterostructure architecture (VEHSA) design for concentrated photovoltaic applications. <i>Solar Energy Materials and Solar Cells</i> , 2018, 181, 46-52.	6.2	18
20	Metastable States in Pressurized Bulk and Mesoporous Germanium. <i>Journal of Physical Chemistry C</i> , 2018, 122, 10929-10938.	3.1	6
21	Fast growth synthesis of mesoporous germanium films by high frequency bipolar electrochemical etching. <i>Electrochimica Acta</i> , 2017, 232, 422-430.	5.2	33
22	Graphene-Mesoporous Si Nanocomposite as a Compliant Substrate for Heteroepitaxy. <i>Small</i> , 2017, 13, 1603269.	10.0	11
23	Measurement of strong photon recycling in ultra-thin GaAs n/p junctions monolithically integrated in high-voltage vertical epitaxial heterostructure architectures with conversion efficiencies exceeding 60%. <i>Physica Status Solidi - Rapid Research Letters</i> , 2017, 11, 1600385.	2.4	27
24	Chemical Composition of Nanoporous Layer Formed by Electrochemical Etching of p-Type GaAs. <i>Nanoscale Research Letters</i> , 2016, 11, 446.	5.7	39
25	High-photovoltage GaAs vertical epitaxial monolithic heterostructures with 20 thin p/n junctions and a conversion efficiency of 60%. <i>Applied Physics Letters</i> , 2016, 109, .	3.3	71
26	Thin n/p GaAs Junctions for Novel High-Efficiency Phototransducers Based on a Vertical Epitaxial Heterostructure Architecture. <i>MRS Advances</i> , 2016, 1, 881-890.	0.9	11
27	Ultrahigh efficiencies in vertical epitaxial heterostructure architectures. <i>Applied Physics Letters</i> , 2016, 108, .	3.3	82
28	Enhanced photocarrier extraction mechanisms in ultra-thin photovoltaic GaAs n/p junctions. <i>Proceedings of SPIE</i> , 2016, , .	0.8	4
29	Advances with vertical epitaxial heterostructure architecture (VEHSA) phototransducers for optical to electrical power conversion efficiencies exceeding 50 percent. <i>Proceedings of SPIE</i> , 2016, , .	0.8	6
30	Focused gas beam injection for efficient ammonia-molecular beam epitaxial growth of III-nitride semiconductors. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2016, 34, .	1.2	1
31	Microstructural evolution of a recrystallized Fe-implanted InGaAsP/InP heterostructure. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2015, 212, 1888-1896.	1.8	3
32	Critical process temperatures for resistive InGaAsP/InP heterostructures heavily implanted by Fe or Ga ions. <i>Nuclear Instruments &amp; Methods in Physics Research B</i> , 2015, 359, 99-106.	1.4	4
33	Approaching the Shockley-Queisser limit: General assessment of the main limiting mechanisms in photovoltaic cells. <i>Journal of Applied Physics</i> , 2015, 117, .	2.5	26
34	Five-volt vertically-stacked, single-cell GaAs photonic power converter. <i>Proceedings of SPIE</i> , 2015, , .	0.8	15
35	Near-infrared emission from mesoporous crystalline germanium. <i>AIP Advances</i> , 2014, 4, 107128.	1.3	6
36	Mesoporous germanium morphology transformation for lift-off process and substrate re-use. <i>Applied Physics Letters</i> , 2013, 102, .	3.3	39

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37	Control of mesoporous silicon initiation by cathodic passivation. <i>Electrochemistry Communications</i> , 2013, 36, 84-87.	4.7	7
38	Mesoporous Germanium formed by bipolar electrochemical etching. <i>Electrochimica Acta</i> , 2013, 88, 256-262.	5.2	35
39	Fabrication of high resistivity cold-implanted InGaAsP photoconductors for efficient pulsed terahertz devices. <i>Optical Materials Express</i> , 2011, 1, 1165.	3.0	25
40	Theoretical and experimental molecular beam angular distribution studies for gas injection in ultra-high vacuum. <i>Journal of Crystal Growth</i> , 2009, 311, 1640-1645.	1.5	9